

EAST [1346.wsp.1]

File View Edit Tools Window Help

☒ L4: (327) electron near3 memory.clm.
☒ L5: (6) (quantum adj dot) with (electron near3 memory).clm.
☒ L6: (10) ((quantum adj dot) with (electron near3 memory)) with gate
☒ L7: (1) "5801401".PN.
☒ **L8: (12) 4 and (quantum near3 dot) with tunneling**
☒ L9: (11) 4 and (quantum near3 dot) with memory

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Browse
 Plural
 Delete Highlight all hit terms initially
 tunneling

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20040076032 A1	20040422	18	Single electron memory device comprising quantum dots between ga	365/145	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20030197168 A1	20031023	12	Emitter with filled zeolite emission layer	257/10	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20030153151 A1	20030814	12	Memory device with quantum dot and method for manufacturing the sa	438/257	257/316;
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20030054624 A1	20030320	12	Quantum dot of single electron memory device and method for fabric	438/590	257/E21.209;
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20020167002 A1	20021114	18	Single electron memory device comprising quantum dots between ga	257/20	257/24;
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20020031649 A1	20020314	12	Quantum dot of single electron memory device and method for fabric	428/209	257/E21.345;
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6670670 B2	20031230	16	Single electron memory device comprising quantum dots between ga	257/316	257/E29.301
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6649966 B2	20031118	11	Quantum dot of single electron memory device and method for fabric	257/314	257/321;
9	<input type="checkbox"/>	<input type="checkbox"/>	US 6597036 B1	20030722	11	Multi-value single electron memory using double-quantum dot and drivin	257/316	257/325;
10	<input type="checkbox"/>	<input type="checkbox"/>	US 6524883 B2	20030225	12	Quantum dot of single electron memory device and method for fabric	438/94	257/315;
11	<input type="checkbox"/>	<input type="checkbox"/>	US 6323504 B1	20011127	15	Single-electron memory device using an electron-hole coulomb blockade	257/14	257/317;
12	<input type="checkbox"/>	<input type="checkbox"/>	US 6660551 A1	20030320	12	Quantum dot of single electron memory device and method for fabric	438/94	257/E21.345;
13	<input type="checkbox"/>	<input type="checkbox"/>	US 6323504 B1	20011127	15	Single-electron memory device using an electron-hole coulomb blockade	257/14	257/E29.301;
14	<input type="checkbox"/>	<input type="checkbox"/>	US 6660551 A1	20030320	12	Quantum dot of single electron memory device and method for fabric	438/94	257/20;
15	<input type="checkbox"/>	<input type="checkbox"/>	US 6660551 A1	20030320	12	Quantum dot of single electron memory device and method for fabric	438/94	257/23;

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☒ Plurals
 Default ☒ Highlight all hit terms initially
 4 and (quantum
 [Icons: Home, Back, Forward, Stop, Reload]

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1	<input type="checkbox"/>	<input type="checkbox"/>	US 20040076032 A1	20040422	18	Single electron memory device comprising quantum dots between ga	365/145	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20030153151 A1	20030814	12	Memory device with quantum dot and method for manufacturing the sa	438/257	257/316; 257/E21.209;
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7	<input type="checkbox"/>	<input type="checkbox"/>	US 6649966 B2	20031118	11	Quantum dot of single electron memory device and method for fabric	257/314	257/315; 257/316;
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6597036 B1	20030722	11	Multi-value single electron memory using double-quantum dot and drivin	257/316	257/315; 257/317;
9	<input type="checkbox"/>	<input type="checkbox"/>	US 6524883 B2	20030225	12	Quantum dot of single electron memory device and method for fabric	438/94	257/E21.345; 257/E29.301;
10	<input type="checkbox"/>	<input type="checkbox"/>	US 6323504 B1	20011127	15	Single-electron memory device using an electron-hole coulomb blockade	257/14	257/20; 257/23;
11	<input type="checkbox"/>	<input type="checkbox"/>	US 5663571 A	19970902	50	Quantum memory	257/17	257/21; 257/22;